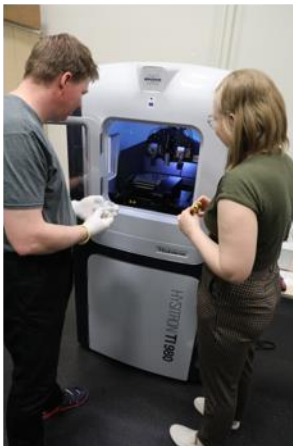
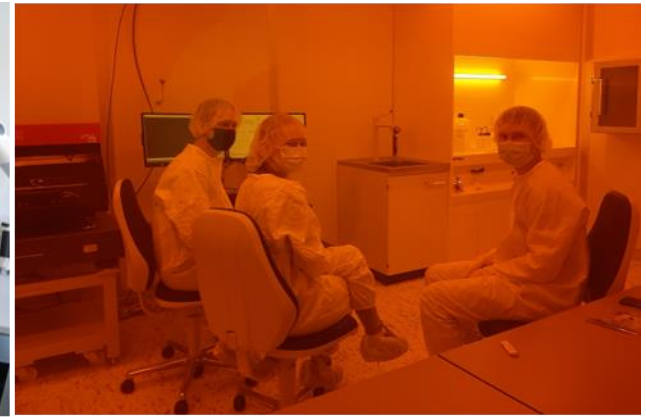
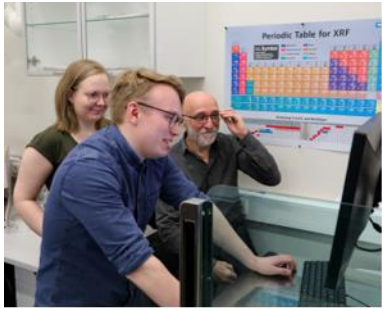




Kaupo Kukli

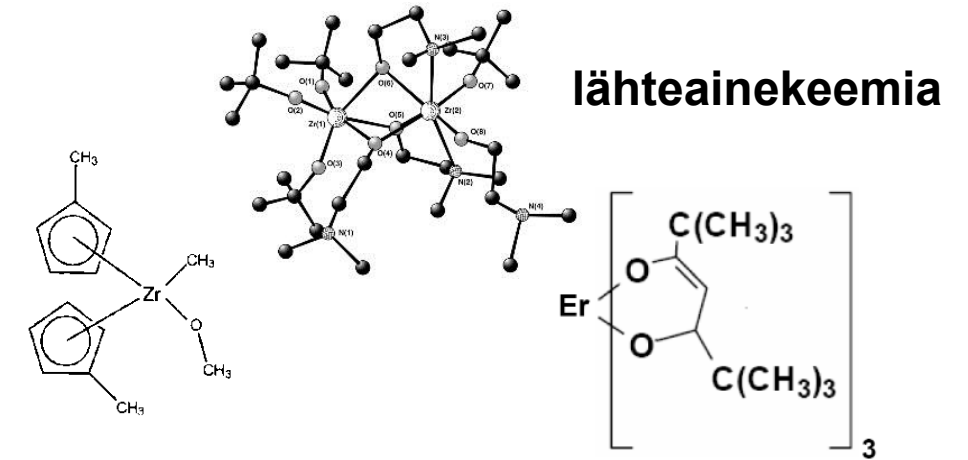
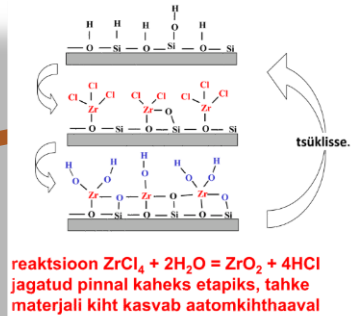
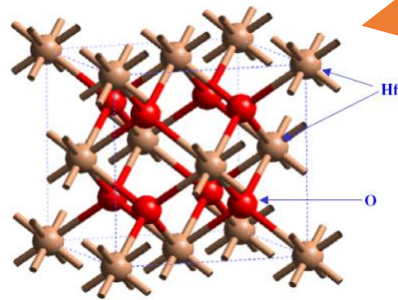
Tartu Ülikool, Füüsika instituut, kiletehnoloogia laboratoorium



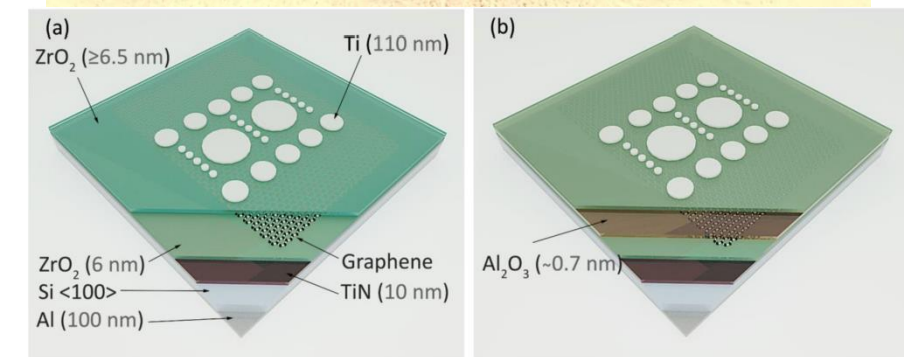
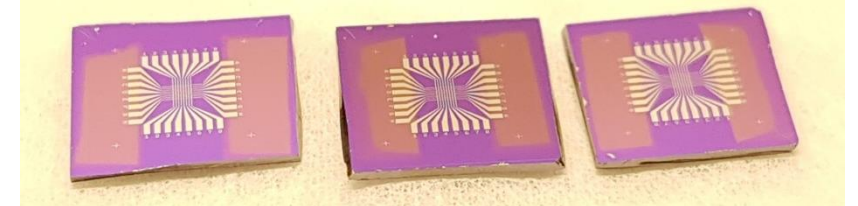
Kiletehnoloogiline teadusarendustöö

kiletehnoloogia kui protsessiinseneeria

tahkisfüüsika
(struktuur, kõvadus,
elastus, defektsus,
polariseeritavus)



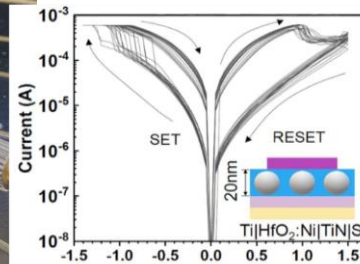
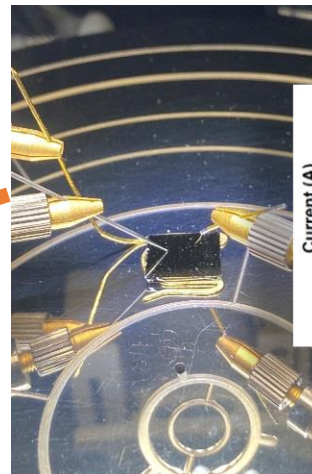
litograafia, kontakteerimine, prototüübid



Kahro et al. doi: 10.1116/6.0000390

funktsionaalsete
omaduste
evalueerimine

publitseerimine,
väitekirjad,
koostöö
partneritega



röntgenfluorestsentspektromeetria



transmissioonelektronmikroskoopia



Volt-ampér ja voltfaradkarakteristika



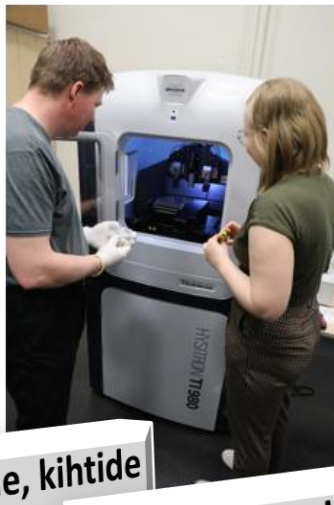
maskivaba fotolitograafia
puhasruumis (ISO klass 5)



aatomkihtsadestusreaktorid



nanoindenteerimine, kihtide
kõvadus ja elastsus



skaneeriv elektronmikroskoopia



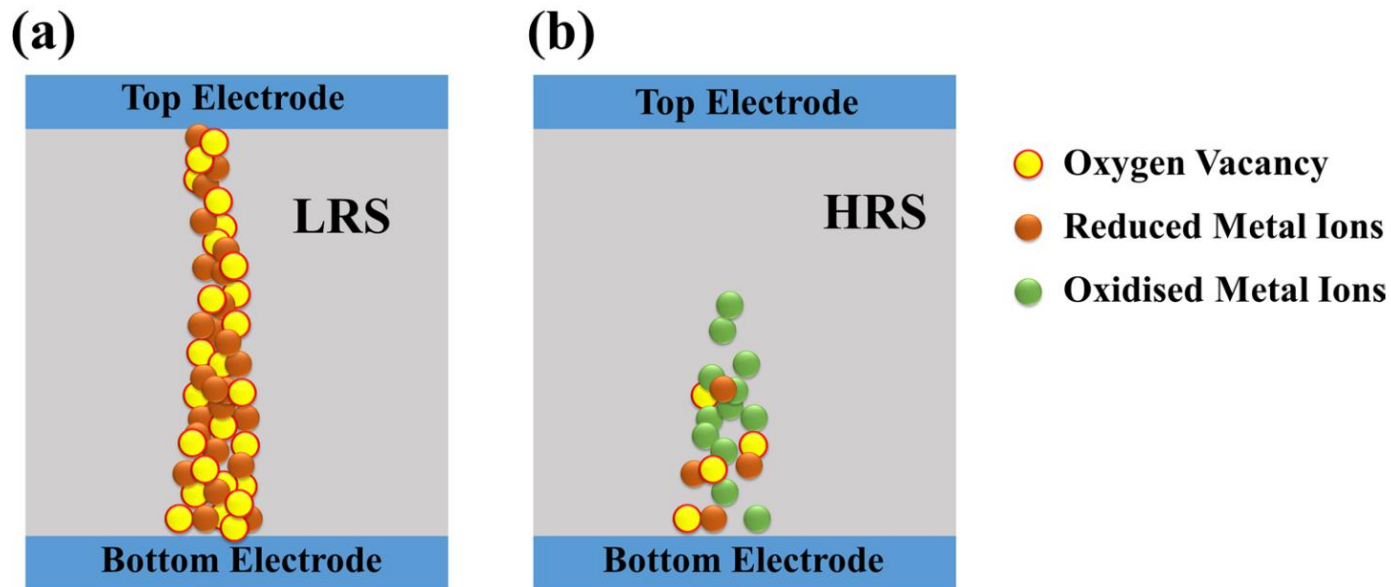
röntgendifraktomeetria



projektijuhtkond

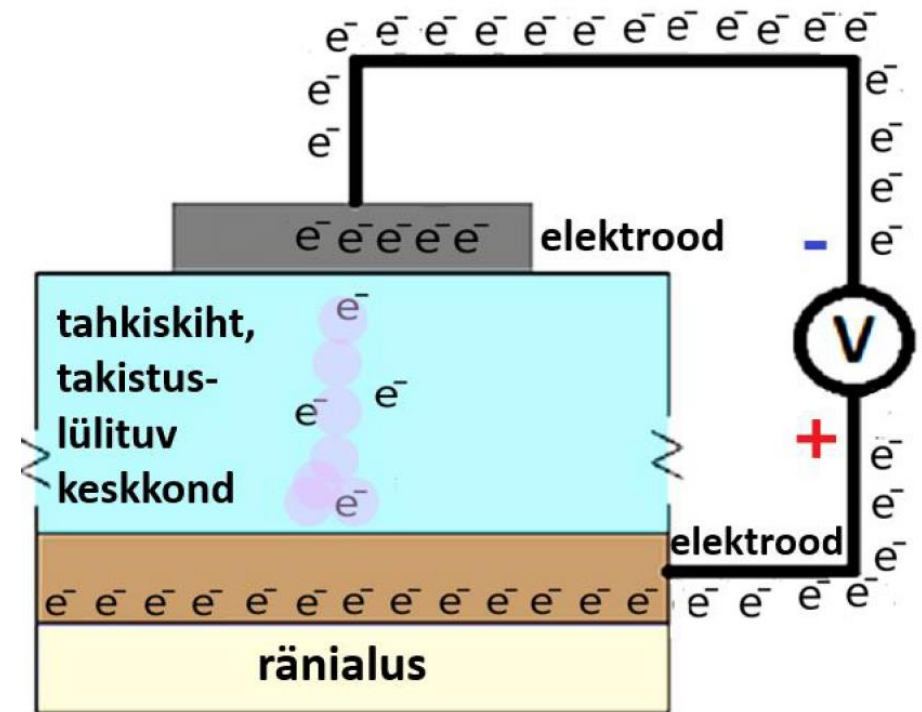
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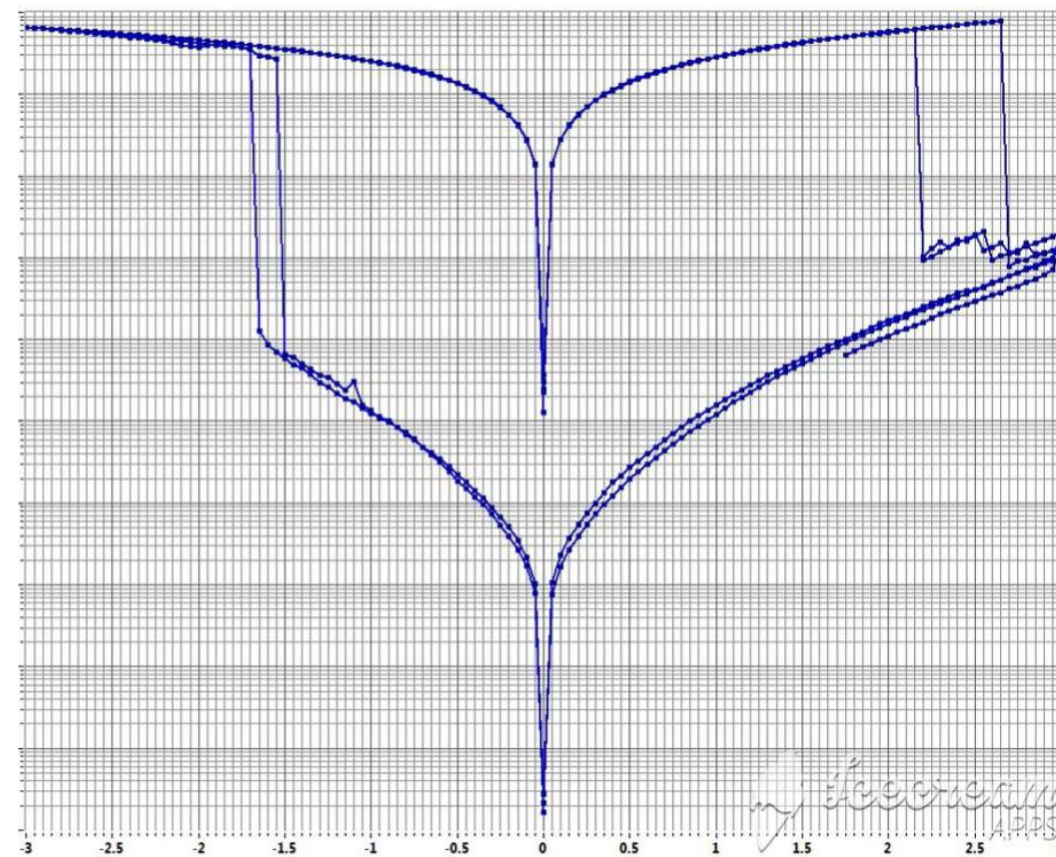
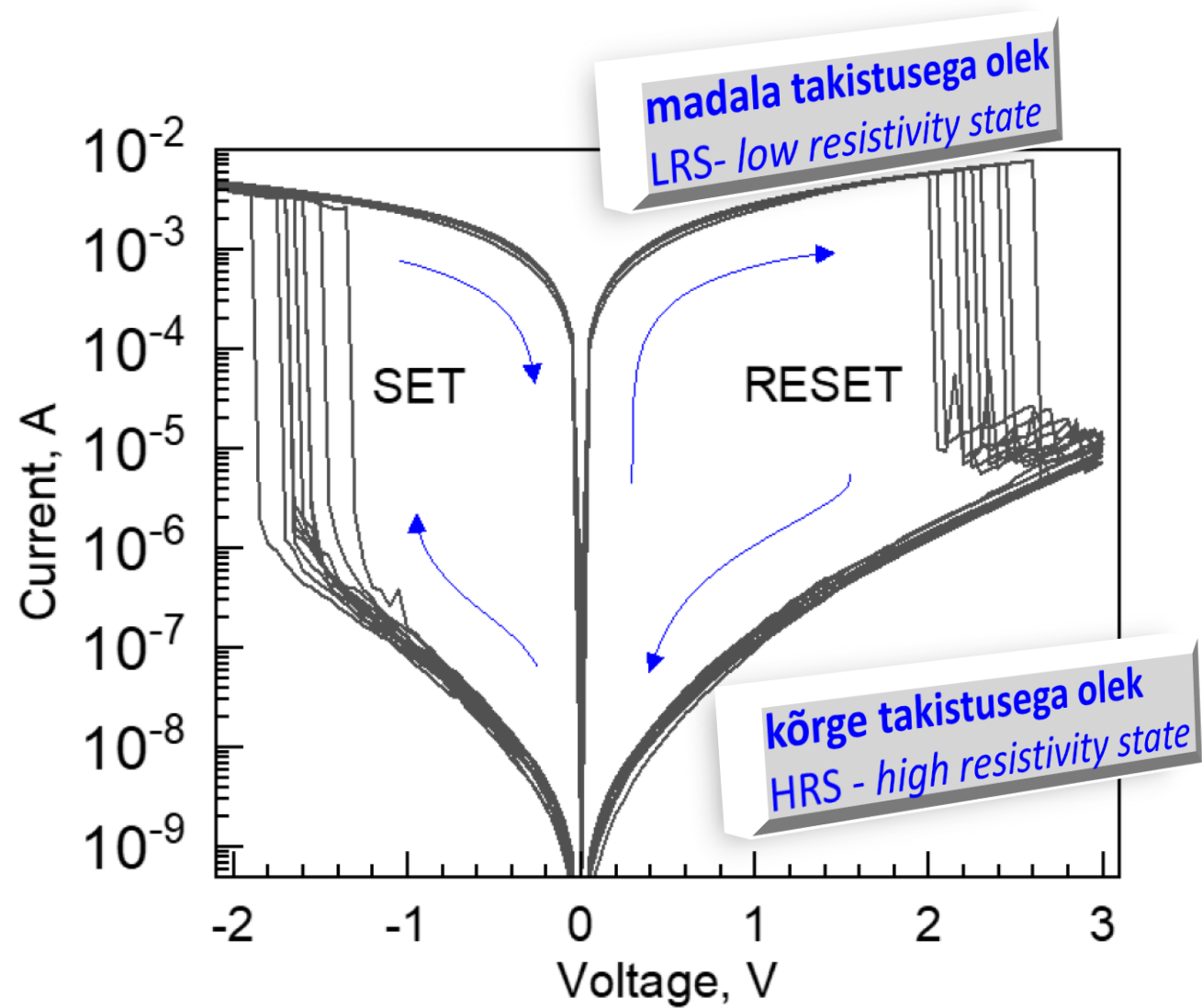
PRG753



Schematic representation of the CF in valence change RS memory

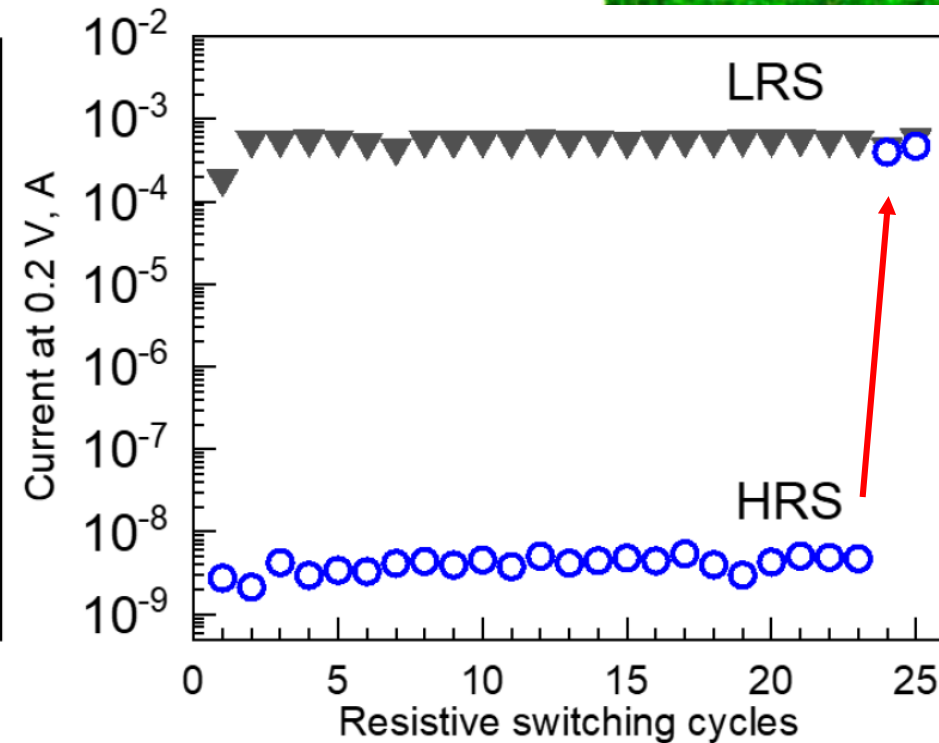
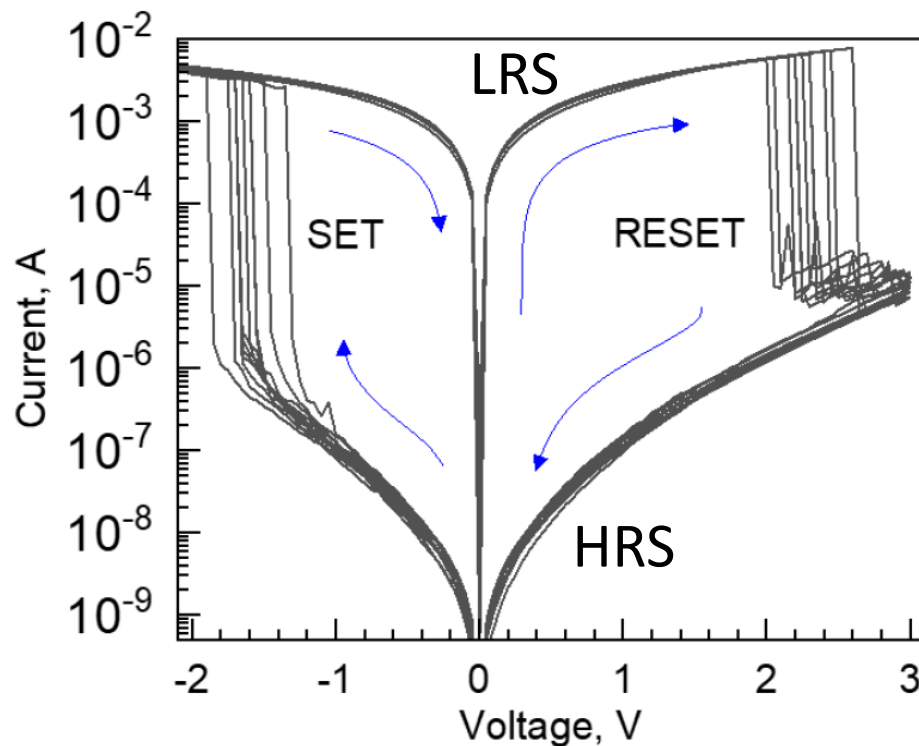
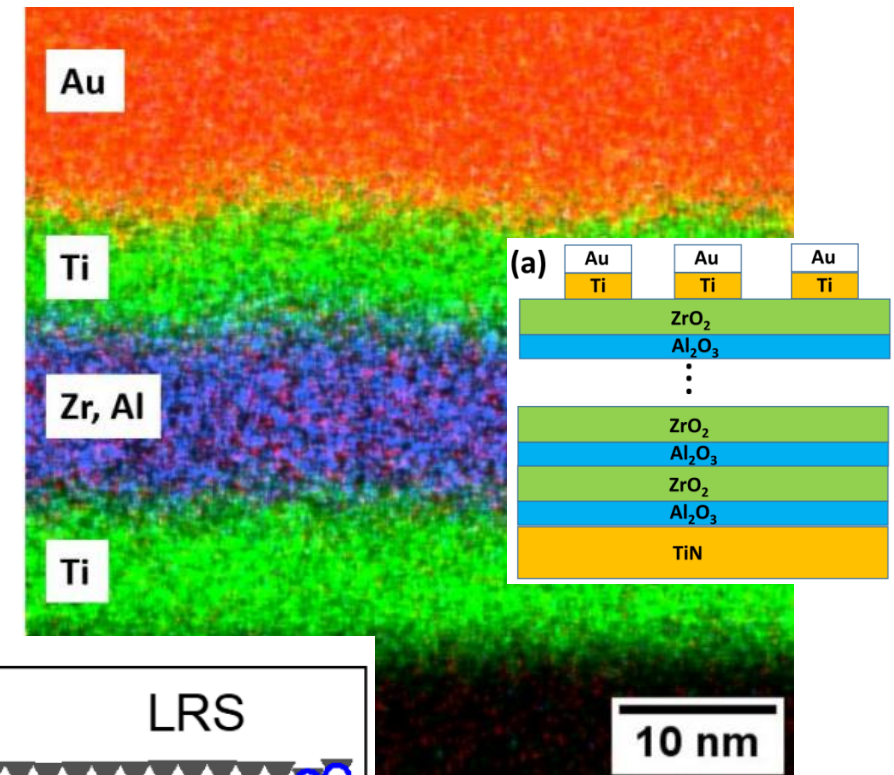
CF – conductive filament; RS – resistive switching





Structure and Electrical Properties of Zirconium-Aluminum-Oxide Films Engineered by Atomic Layer Deposition

Joonas Merisalu ^{*}, Taivo Jõgiaas, **Toomas Daniel Viskus**, Arne Kasikov, Peeter Ritslaid, Tanel Käämbre, Aivar Tarre, Jekaterina Kozlova, Hugo Mändar, Aile Tamm, Jaan Aarik and Kaupo Kukli



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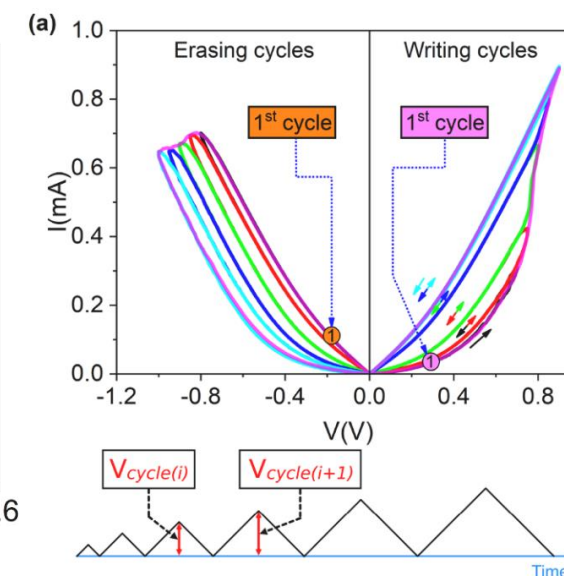
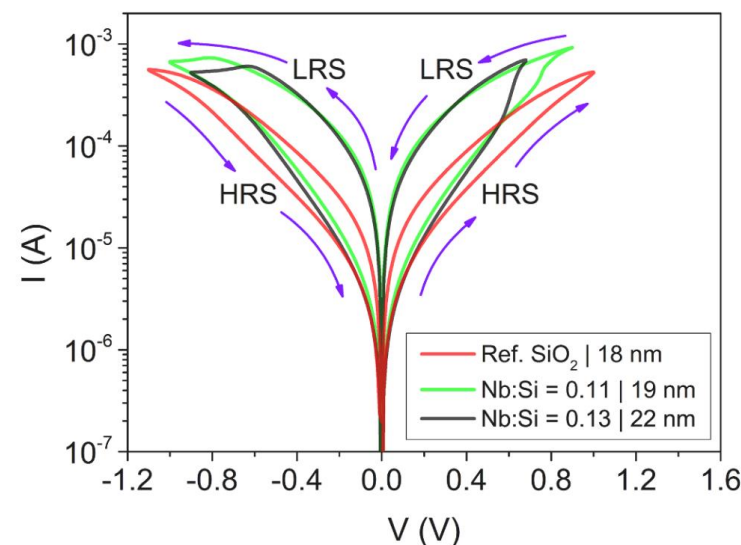
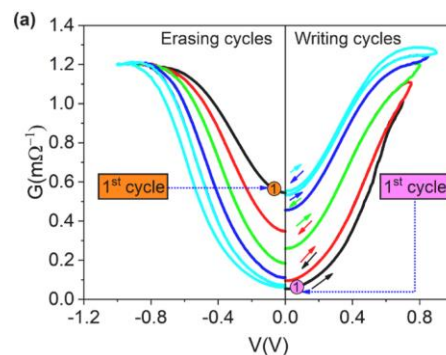
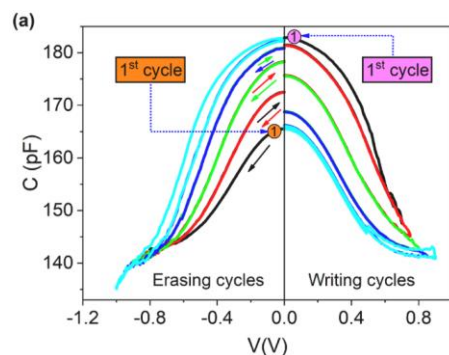
Analysis of the performance of Nb₂O₅-doped SiO₂-based MIM devices for memory and neural computation applications

Ó.G. Ossorio^a, G. Vinuesa^a, H. García^a, B. Sahelices^a, S. Dueñas^a, H. Castán^{a,*}, M. Ritala^b,
M. Leskela^b, M. Kemell^b, K. Kukli^c

^a Department of Electronics, University of Valladolid, Paseo de Belén 15, Valladolid E-47011, Spain

^b Department of Chemistry, University of Helsinki, P.O.Box 55, Helsinki FI-00014, Finland

^c Institute of Physics, University of Tartu, W. Ostwald 1, Tartu 50411, Estonia

Si₂(NH₄)₆

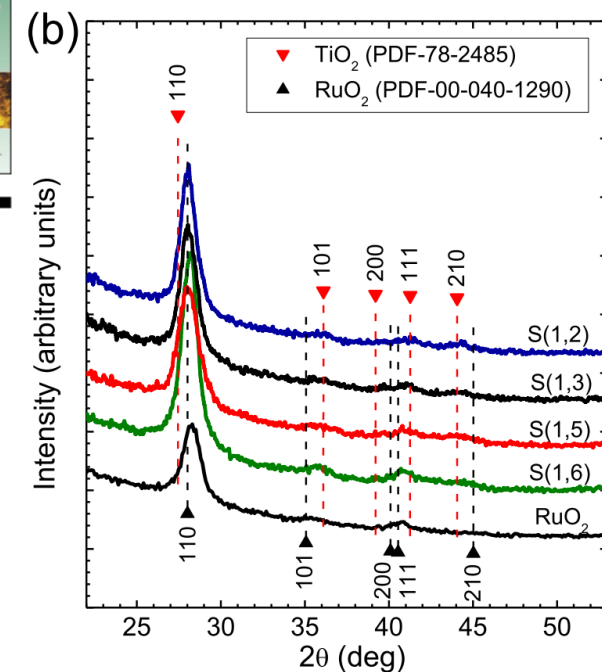
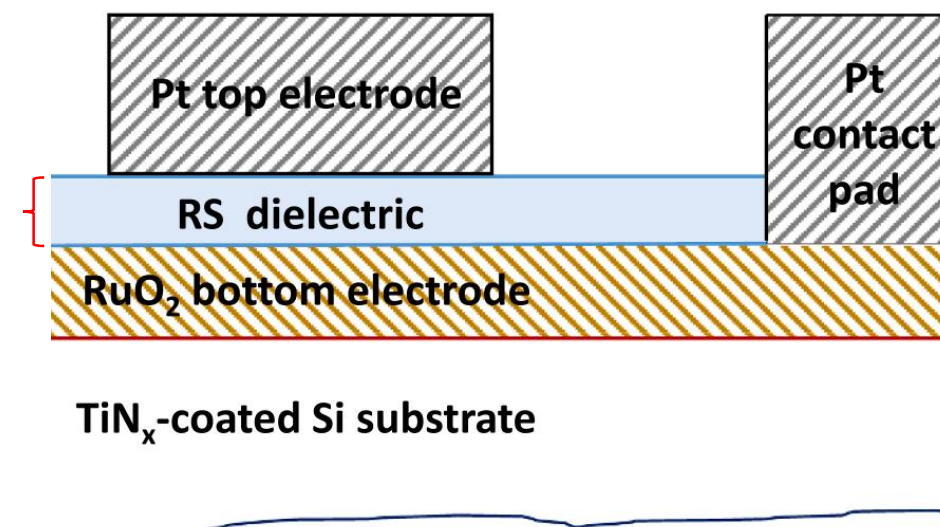
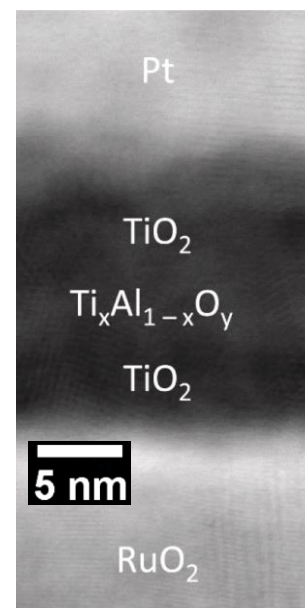
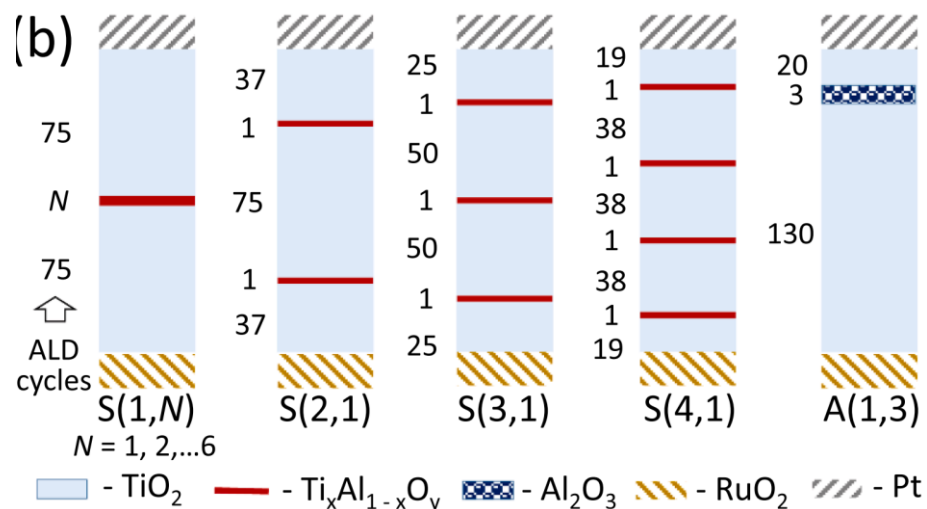
heksakisetiülaminodisilaan
ja osoon



Engineering of atomic layer deposition process for titanium-aluminum-oxide based resistively switching medium

Joonas Merisalu^{*}, Tõnis Arroval, Aarne Kasikov, Jekaterina Kozlova, Mihkel Rähn, Peeter Ritslaid, Jaan Aarik, Aile Tamm, Kaupo Kukli

Institute of Physics, University of Tartu, W. Ostwaldi 1, EE50411 Tartu, Estonia

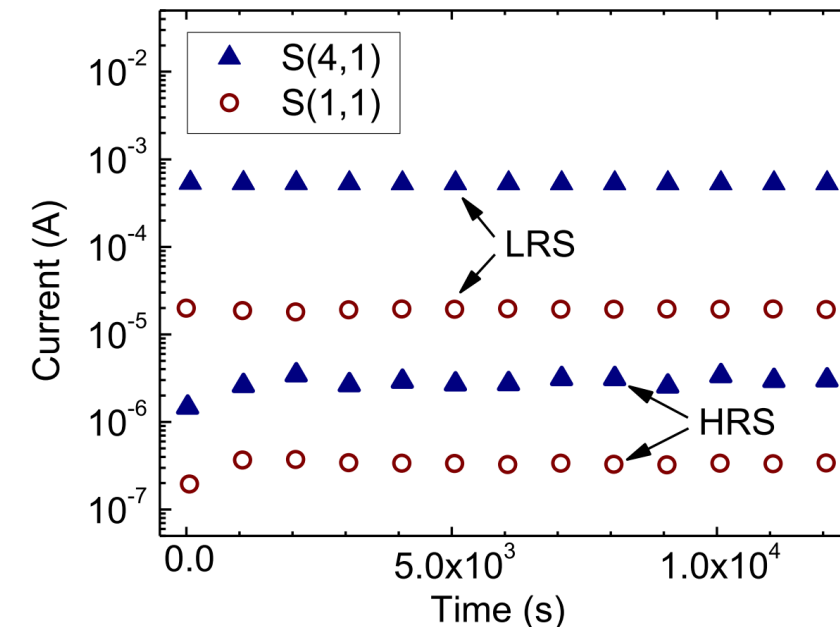
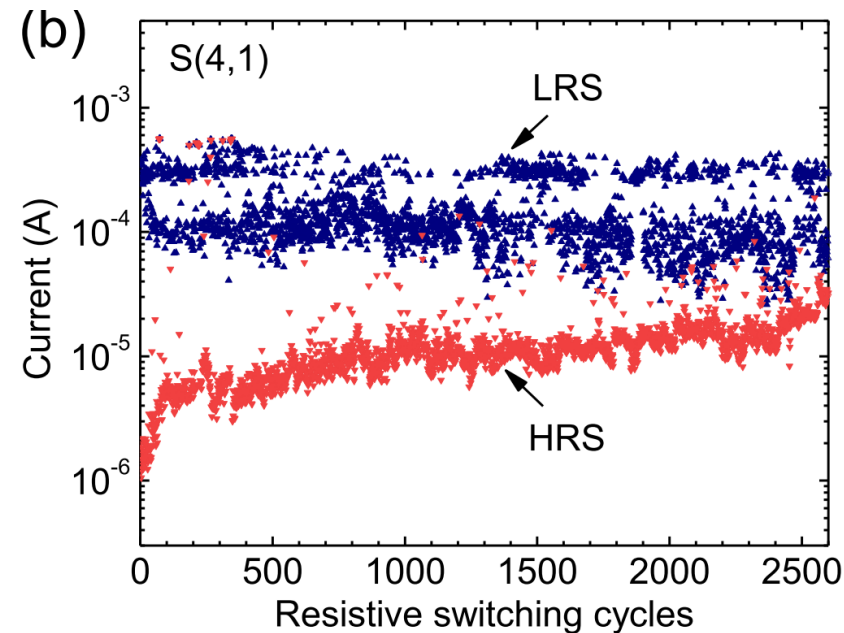
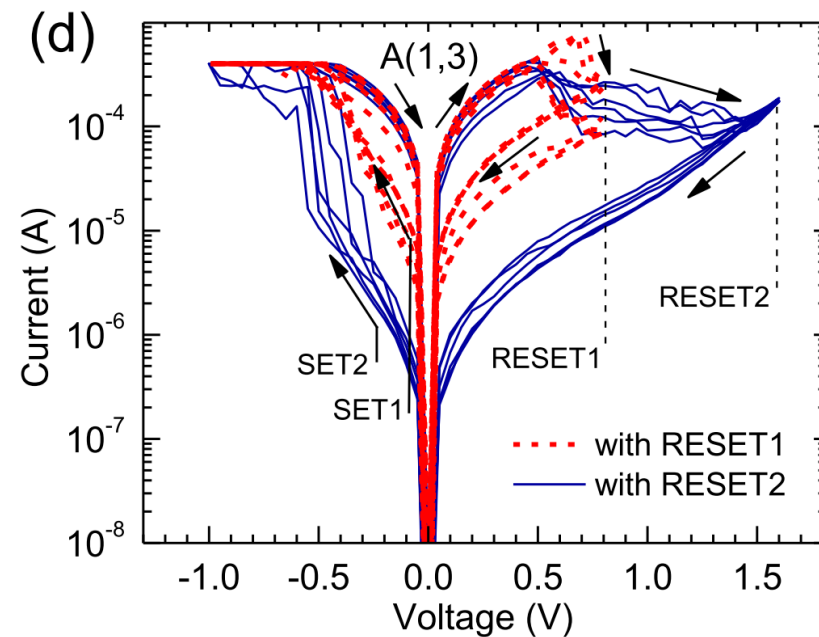
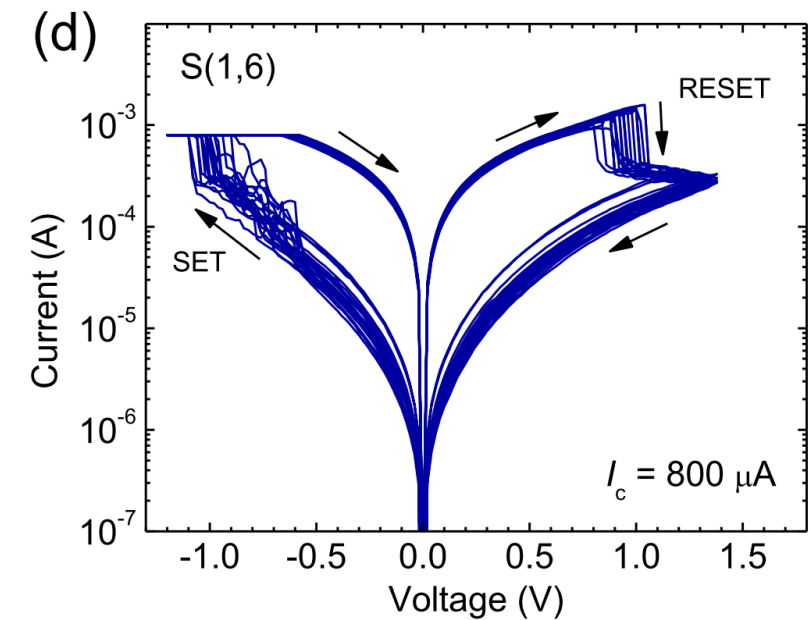




Engineering of atomic layer deposition process for titanium-aluminum-oxide based resistively switching medium

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Hafnium Oxide/Graphene/Hafnium Oxide-Stacked Nanostructures as Resistive Switching Media

Tauno Kahro,* Aivar Tarre, Tanel Käämbre, Helle-Mai Piirsoo, Jekaterina Kozlova, Peeter Ritslaid, Aarne Kasikov, Taivo Jõgiaas, Guillermo Vinuesa, Salvador Dueñas, Helena Castán, Aile Tamm, and Kaupo Kukli



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